

## 2N6421-2N6422

High-reliability discrete products and engineering services since 1977

### PNP SILICON HIGH POWER TRANSISTORS

### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### MAXIMUM RATINGS

| Ratings   | Symbol                           | 2N6421      | 2N6422 | Unit |  |
|---|----------------------------------|-------------|--------|------|--|
| Collector-Emitter Voltage                         | V <sub>CEO</sub>                 | 250         | 300    | Vdc  |  |
| Collector-Base Voltage                            | V <sub>CBO</sub>                 | 375         | 500    | Vdc  |  |
| Collector-Emitter Voltage                         | VCER                             | 300         | 400    | Vdc  |  |
| Emitter-Base Voltage                              | V <sub>EBO</sub>                 | 6.0         |        | Vdc  |  |
| Base Current                                      | IB                               | 1.0         |        | Adc  |  |
| Collector Current                                 | lc                               | 2.0         |        | Adc  |  |
| Total Power Dissipation                           | D                                | 2           | F      | w    |  |
| $T_c = 100^{\circ}C^{(2)}$                        | ΡŢ                               | 35          |        |      |  |
| Operating & Storage Junction Temperature Range    | T <sub>J</sub> ,T <sub>stg</sub> | -65 to +200 |        | °C   |  |
| Maximum Thermal Resistance Junction to Case       | Reac                             | 5.0         |        | °C/W |  |
| Note 1: Derate linearly @ 14 PEMW/PC for T > 2E°C |                                  |             |        |      |  |

Note 1: Derate linearly @ 14.85mW/°C for T<sub>A</sub> > 25°C

Note 2: Derate linearly @  $200 \text{mW/}^{\circ}\text{C}$  for  $T_{c} > 25^{\circ}\text{C}$ 

#### **ELECTRICAL CHARACTERSITICS** (T<sub>A</sub> = 25°C unless otherwise specified)

| Characteristics                                      |        | Symbol          | Min. | Max. | Unit     |  |
|--|--------|-----------------|------|------|----------|--|
| OFF CHARACTERISTICS                                  |        |                 |      |      |          |  |
| Collector-Emitter Voltage                            | 2N6421 | Masaa           | 250  |      | Vdc      |  |
| I <sub>C</sub> = 10mA                                | 2N6422 | V (BR)CEO       | 300  |      | Vuc      |  |
| Collector-Base Breakdown Voltage                     | 2N6421 | Maria           | 375  |      | ) (de    |  |
| I <sub>C</sub> = 15mA                                | 2N6422 | V (BR)CER       | 500  |      | vdc      |  |
| Collector-Emitter Cutoff Current                     |        |                 |      |      | m A da   |  |
| V <sub>CE</sub> = -150V                              |        | ICEO            |      | 5.0  | maac     |  |
| Collector-Emitter Cutoff Current                     |        |                 |      |      |          |  |
| V <sub>CE</sub> = 300 Vdc, V <sub>BE</sub> = -1.5Vdc | 2N6421 | ICEX            |      | 1.0  | mAdc     |  |
| $V_{CE}$ = 300 Vdc, $V_{BE}$ = -1.5Vdc               | 2N6422 |                 |      | 1.0  |          |  |
| Emitter-Base Cutoff Current                          |        |                 |      |      | ma A dia |  |
| V <sub>EB</sub> = 6.0 Vdc                            |        | IEBO            |      | 0.5  | made     |  |
| Forward Current Transfer Ratio                       |        |                 |      |      |          |  |
| $I_{C}$ = 1.0Adc, $V_{CE}$ = 10.0 Vdc                |        | h <sub>FE</sub> | 25   | 100  |          |  |
| I <sub>C</sub> = 100mAdc, V <sub>CE</sub> = 10.0 Vdc |        |                 | 40   |      |          |  |
| Collector-Emitter Saturation Voltage                 |        |                 |      |      | ) (de    |  |
| I <sub>C</sub> = 1.0Adc, I <sub>B</sub> = 0.125 Adc  |        | VCE(sat)        |      | 0.75 | Vac      |  |
| Base-Emitter Saturation Voltage                      |        | N               |      |      | Vde      |  |
| I <sub>C</sub> = 1.0Adc, I <sub>B</sub> = 0.1Adc     |        | V BE(SAT)       |      | 1.4  | vac      |  |



High-reliability discrete products and engineering services since 1977

## 2N6421-2N6422

### PNP SILICON HIGH POWER TRANSISTORS

| Characteristics  | Symbol             | Min. | Max. | Unit |  |
|--|--------------------|------|------|------|--|
| DYNAMIC CHARACTERISTICS  |                    |      |      |      |  |
| $\label{eq:magnitude} \begin{array}{l} \mbox{Magnitude of Common Emitter Small-Signal Short Circuit Forward} \\ \mbox{Current Transfer Ratio} \\ \mbox{I}_c = 200 \mbox{mAdc}, \mbox{V}_{CE} = 10.0 \mbox{ Vdc}, \mbox{f} = 5.0 \mbox{MHz} \end{array}$  | lh <sub>FE</sub> I | 3.0  | 15   |      |  |
| Small Signal Short Circuit Forward Transfer Ratio<br>I <sub>c</sub> = 1.0 Adc, V <sub>CE</sub> = 10.0 Vdc, f = 1.0kHz  | h <sub>fe</sub>    | 25   | 200  |      |  |
| Output Capacitance $V_{CB}$ = 10Vdc, $I_E$ = 0, 100kHz $\leq$ f $\leq$ 1.0MHz  | C <sub>obo</sub>   |      | 120  | pF   |  |
| SWITCHING CHARACTERISTICS  |                    |      |      |      |  |
| Turn-On Time $V_{cc}$ = 30Vdc, $I_c$ = 1.0Adc, $I_B$ = 100mAdc, $R_c$ = 29 $\Omega$  | t <sub>on</sub>    |      | 3.0  | μs   |  |
| Turn-Off Time $V_{cc}$ = 30Vdc, I <sub>c</sub> = 0.5Adc, I <sub>B</sub> = -IB = 100mAdc, R <sub>c</sub> = 29 $\Omega$  | t <sub>off</sub>   |      | 7.0  | μs   |  |
| SAFE OPERATING AREA  |                    |      |      |      |  |
| Dc Tests<br>$T_c = 25^{\circ}C, 1 \text{ cycle, } t = 1.0\text{s}$<br>Test 1<br>$V_{CE} = 17.5 \text{Vdc, } I_c = 2.0 \text{Adc}$<br>Test 2<br>$V_{CE} = 100 \text{Vdc, } I_c = 350 \text{mAdc}$<br>Test 3<br>$V_{CE} = 250 \text{Vdc, } I_c = 37 \text{mAdc} (2N6421)$<br>$V_{CE} = 300 \text{Vdc, } I_c = 17 \text{mAdc} (2N6422)$ |                    |      |      |      |  |

Note 3: Pulse Test: Pulse Width =  $300\mu s$ , Duty Cycle  $\leq 2.0\%$ 



High-reliability discrete products and engineering services since 1977

# 2N6421-2N6422

### PNP SILICON HIGH POWER TRANSISTORS

#### MECHANICAL CHARACTERISTICS

| Case     | TO-66         |
|----------|---------------|
| Marking  | Alpha-numeric |
| Polarity | See below     |



|     | TO-66  |       |        |        |  |
|-----|--------|-------|--------|--------|--|
| Dim | Inches |       | Millim | neters |  |
|     | Min    | Max   | Min    | Max    |  |
| BL  | 1.205  | 1.280 | 30.60  | 32.50  |  |
| CD  | 0.445  | 0.557 | 11.303 | 14.148 |  |
| СН  | 0.257  | 0.284 | 6.540  | 7.220  |  |
| LL  | 0.374  | 0.413 | 9.500  | 10.50  |  |
| BW  | 0.680  | 0.727 | 17.26  | 18.46  |  |
| LD  | 0.030  | 0.036 | 0.760  | 0.920  |  |
| HT  | 0.054  | 0.065 | 1.380  | 1.650  |  |
| MHS | 0.951  | 0.976 | 24.16  | 24.78  |  |
| S1  | 0.545  | 0.614 | 13.84  | 15.60  |  |
| HD  | 0.131  | 0.154 | 3.320  | 3.920  |  |
| PS  | 0.191  | 0.210 | 4.860  | 5.340  |  |